# Younghee Lee

## List of Publications by Citations

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

| 23 | 1,038 | 19 | 25 |
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| papers | citations | h-index | g-index |
| 25 | 1,181 | 8 | 4.95 |
| ext. papers | ext. citations | avg, IF | L-index |

| # | Paper | IF | Citations |
|---|---|---|---|
| 23 | Atomic layer etching of Al2O3 using sequential, self-limiting thermal reactions with Sn(acac)2 and hydrogen fluoride. *ACS Nano*, **2015**, 9, 2061-70 | 16.7 | 104 |
| 22 | Surface-coating regulated lithiation kinetics and degradation in silicon nanowires for lithium ion battery. *ACS Nano*, **2015**, 9, 5559-66 | 16.7 | 99 |
| 21 | Prospects for Thermal Atomic Layer Etching Using Sequential, Self-Limiting Fluorination and Ligand-Exchange Reactions. *ACS Nano*, **2016**, 10, 4889-94 | 16.7 | 90 |
| 20 | Atomic Layer Etching of HfO2Using Sequential, Self-Limiting Thermal Reactions with Sn(acac)2and HF. *ECS Journal of Solid State Science and Technology*, **2015**, 4, N5013-N5022 | 2 | 70 |
| 19 | Trimethylaluminum as the Metal Precursor for the Atomic Layer Etching of Al2O3 Using Sequential, Self-Limiting Thermal Reactions. *Chemistry of Materials*, **2016**, 28, 2994-3003 | 9.6 | 65 |
| 18 | Selectivity in Thermal Atomic Layer Etching Using Sequential, Self-Limiting Fluorination and Ligand-Exchange Reactions. *Chemistry of Materials*, **2016**, 28, 7657-7665 | 9.6 | 63 |
| 17 | Atomic Layer Deposition of AlF3 Using Trimethylaluminum and Hydrogen Fluoride. *Journal of Physical Chemistry C*, **2015**, 119, 14185-14194 | 3.8 | 59 |
| 16 | Thermal Atomic Layer Etching of Titanium Nitride Using Sequential, Self-Limiting Reactions: Oxidation to TiO2 and Fluorination to Volatile TiF4. *Chemistry of Materials*, **2017**, 29, 8202-8210 | 9.6 | 52 |
| 15 | Mechanism of Thermal Al2O3 Atomic Layer Etching Using Sequential Reactions with Sn(acac)2 and HF. *Chemistry of Materials*, **2015**, 27, 3648-3657 | 9.6 | 50 |
| 14 | Coating Solution for High-Voltage Cathode: AlF Atomic Layer Deposition for Freestanding LiCoO Electrodes with High Energy Density and Excellent Flexibility. *ACS Applied Materials & Interfaces*, **2017**, 9, 9614-9619 | 9.5 | 47 |
| 13 | Atomic Layer Deposition of LiOH and Li2CO3 Using Lithium t-Butoxide as the Lithium Source. *ECS Transactions*, **2010**, 33, 223-229 | 1 | 47 |
| 12 | Atomic Layer Deposition of Metal Fluorides Using HFPyridine as the Fluorine Precursor. *Chemistry of Materials*, **2016**, 28, 2022-2032 | 9.6 | 44 |
| 11 | Molecular layer deposition of aluminum alkoxide polymer films using trimethylaluminum and glycidol. *Langmuir*, **2011**, 27, 15155-64 | 4 | 39 |
| 10 | Atomic Layer Etching of AlF3 Using Sequential, Self-Limiting Thermal Reactions with Sn(acac)2 and Hydrogen Fluoride. *Journal of Physical Chemistry C*, **2015**, 119, 25385-25393 | 3.8 | 31 |
| 9 | Molecular Layer Deposition of Conductive Hybrid Organic-Inorganic Thin Films Using Diethylzinc and Hydroquinone. *ECS Transactions*, **2010**, 33, 191-195 | 1 | 30 |
| 8 | Thermal atomic layer etching of HfO2 using HF for fluorination and TiCl4 for ligand-exchange. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2018**, 36, 061504 | 2.9 | 29 |
| 7 | Thermal Atomic Layer Etching of Al2O3, HfO2, and ZrO2 Using Sequential Hydrogen Fluoride and Dimethylaluminum Chloride Exposures. *Journal of Physical Chemistry C*, **2019**, 123, 18455-18466 | 3.8 | 25 |

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| 6 | Cross-linked aluminum dioxybenzene coating for stabilization of silicon electrodes. *Nano Energy*, **2016**, 22, 202-210 | 17.1 | 24 |
| 5 | In Situ Thermal Atomic Layer Etching for Sub-5 nm InGaAs Multigate MOSFETs. *Nano Letters*, **2019**, 19, 5159-5166 | 11.5 | 19 |
| 4 | First Transistor Demonstration of Thermal Atomic Layer Etching: InGaAs FinFETs with sub-5 nm Fin-width Featuring in situ ALE-ALD **2018**, | | 17 |
| 3 | Thermal etching of AlF3 and thermal atomic layer etching of Al2O3. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2020**, 38, 022603 | 2.9 | 13 |
| 2 | Mitigating irreversible capacity losses from carbon agents via surface modification. *Journal of Power Sources*, **2015**, 275, 605-611 | 8.9 | 12 |
| 1 | Thermal Atomic Layer Etching of Gallium Oxide Using Sequential Exposures of HF and Various Metal Precursors. *Chemistry of Materials*, **2020**, 32, 5937-5948 | 9.6 | 8 |